

20 V, single N-channel Trench MOSFET 20 January 2016

**Product data sheet** 

### 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Fast switching
- Trench MOSFET technology
- Low threshold voltage
- Ultra thin package profile with 0.37 mm height
- ElectroStatic Discharge (ESD) protection: 2 kV HBM

#### 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	e T <sub>j</sub> = 25 °C		-	-	20	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	1	А
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C		-	290	350	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

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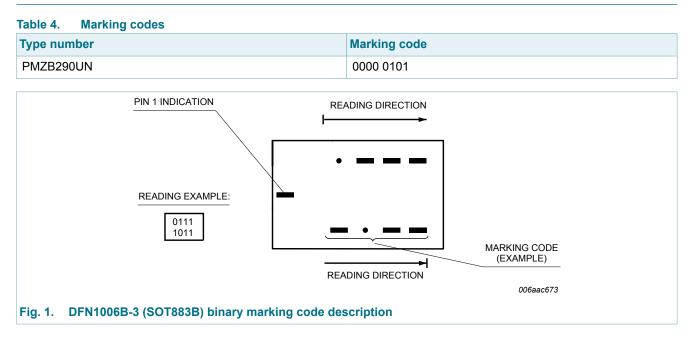
### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1	D
2	S	source	2	
3	D	drain	Transparent top view DFN1006B-3 (SOT883B)	G S 017aaa255

### 6. Ordering information

Table 3. Ordering information						
Type number	Package	;kage				
	Name	Description	Version			
PMZB290UN	DFN1006B-3	DFN1006B-3: leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B			

### 7. Marking



#### 20 V, single N-channel Trench MOSFET

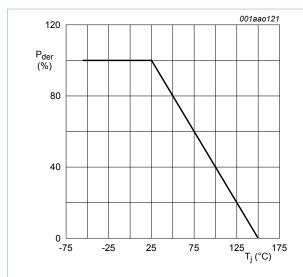
### 8. Limiting values

#### Table 5.Limiting values

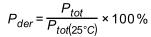
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	20	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	$V_{GS}$ = 4.5 V; $T_{amb}$ = 25 °C	[1]	-	1	А
		$V_{GS}$ = 4.5 V; $T_{amb}$ = 100 °C	[1]	-	0.6	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	4	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T <sub>sp</sub> = 25 °C		-	2700	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode		1			
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.67	А

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.







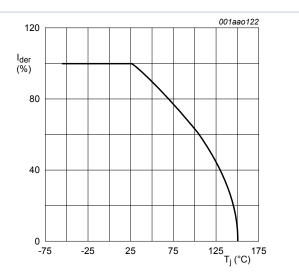
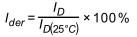
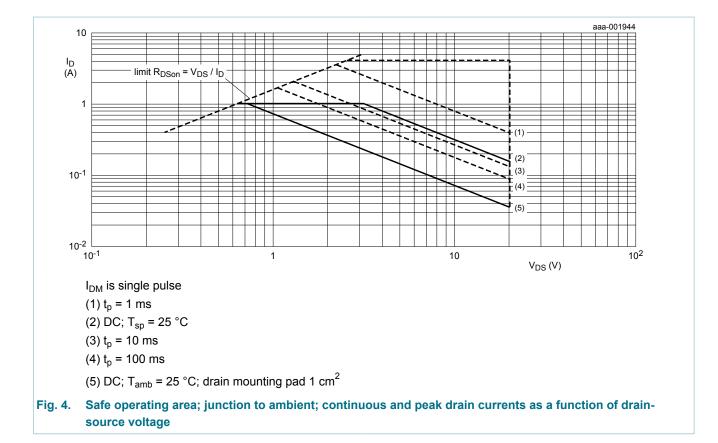


Fig. 3. Normalized continuous drain current as a function of junction temperature



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#### 9. Thermal characteristics

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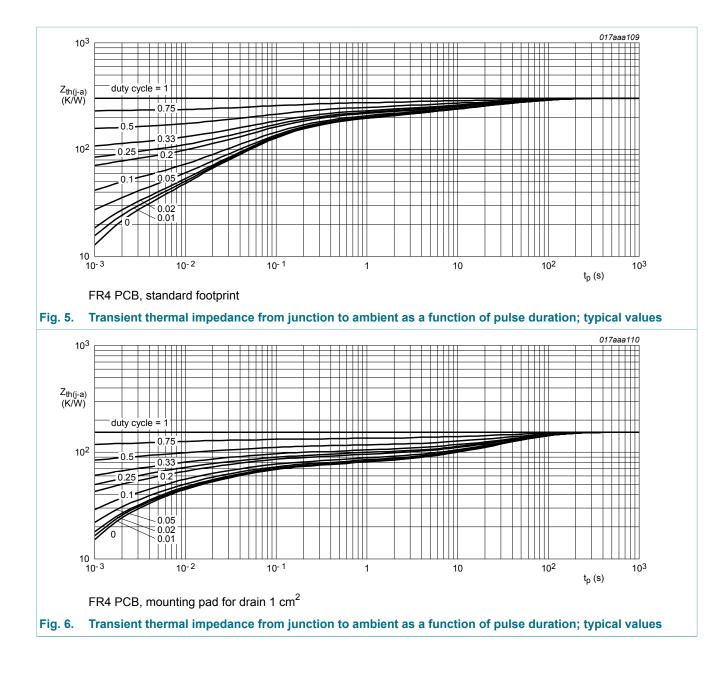
Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	305	360	K/W
			[2]	-	150	175	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	40	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

### PMZB290UN

#### 20 V, single N-channel Trench MOSFET



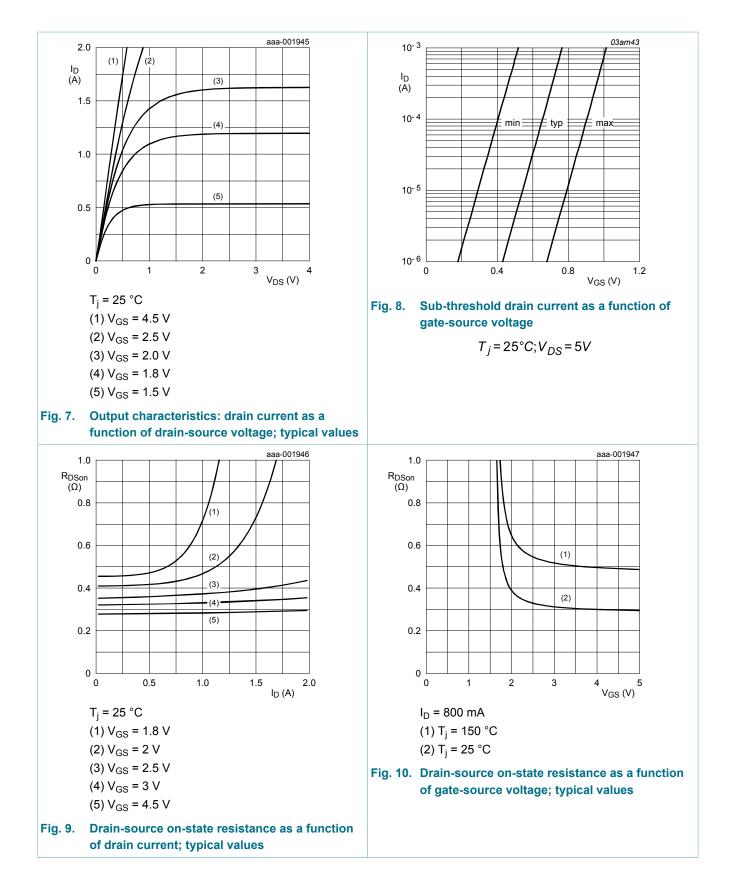
#### 20 V, single N-channel Trench MOSFET

### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = 10 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	20	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	I <sub>D</sub> = 250 μA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	0.45	0.7	0.95	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	5	μA
		$V_{GS}$ = -8 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-5	μA
		$V_{GS}$ = 4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
		$V_{GS}$ = 2.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -2.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C	-	290	350	mΩ
	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 150 °C	-	460	560	mΩ
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 25 °C	-	360	450	mΩ
		V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 75 mA; T <sub>j</sub> = 25 °C	-	460	650	mΩ
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 5 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C	-	5.8	-	S
Dynamic ch	aracteristics	· · · · ·	I			
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 1 A; V <sub>GS</sub> = 4.5 V;	-	0.89	1.2	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.13	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.18	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 20 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	45	68	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	11	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	7	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 10 V; $R_L$ = 10 $\Omega$ ; $V_{GS}$ = 4.5 V;	-	4.5	9	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C	-	10	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	18.5	37	ns
t <sub>f</sub>	fall time		-	5	-	ns
Source-drai	in diode			1	1	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 300 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.75	1.2	V

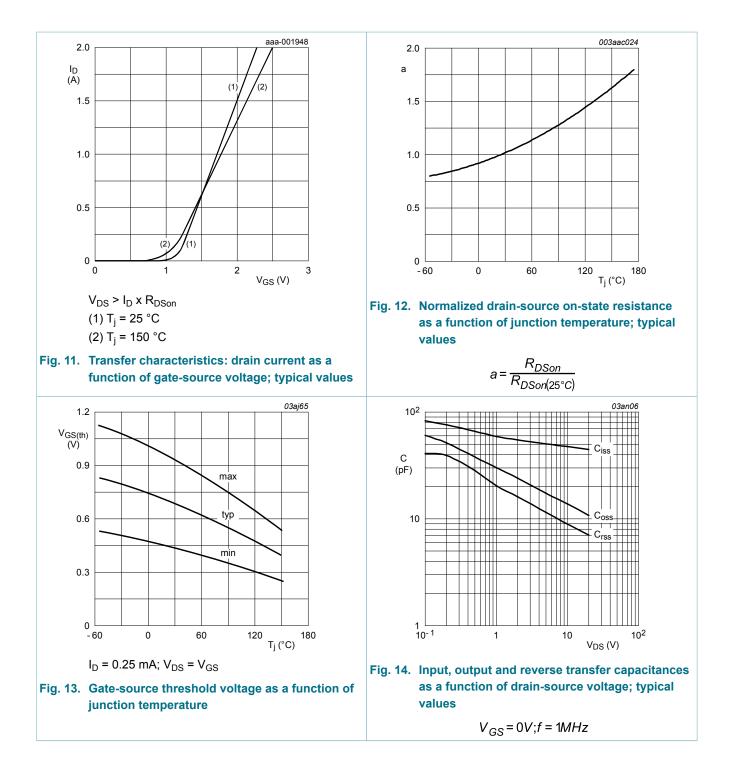
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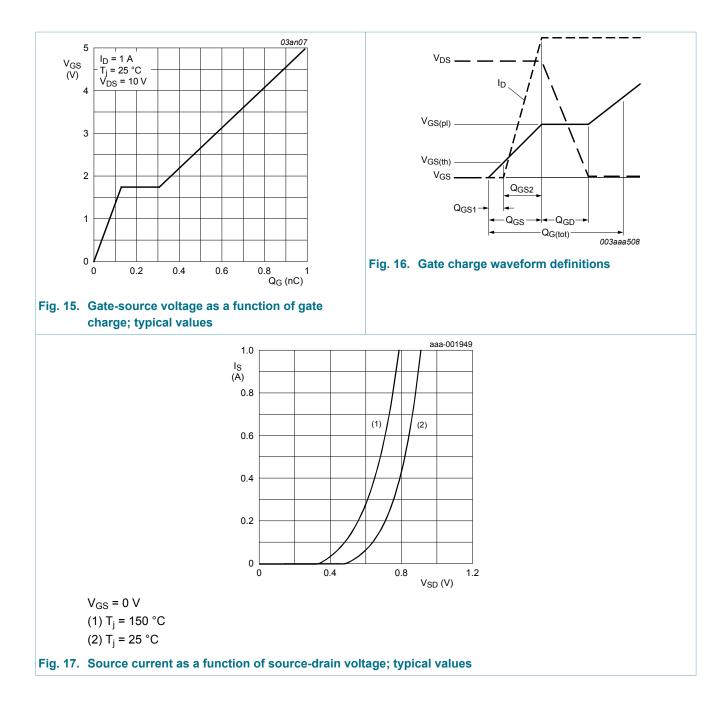
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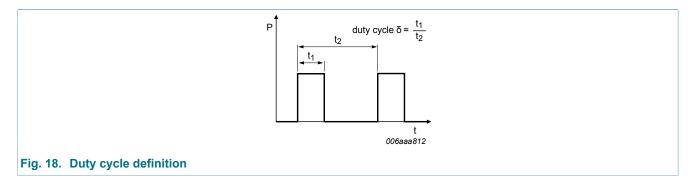
### PMZB290UN

#### 20 V, single N-channel Trench MOSFET

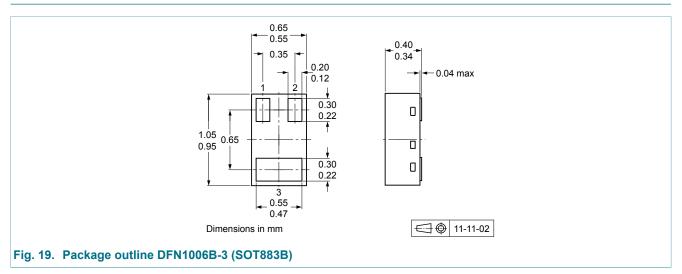


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### 11. Test information



### 12. Package outline



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### **13. Soldering**

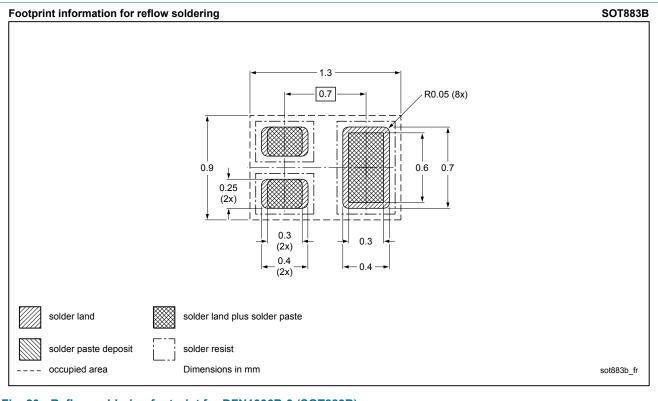


Fig. 20. Reflow soldering footprint for DFN1006B-3 (SOT883B)

#### 20 V, single N-channel Trench MOSFET

### 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMZB290UN v.2	20160120	Product data sheet	-	PMZB290UN v.1		
Modifications:	<ul> <li>values for gate leak</li> </ul>	age current and forward	transconductance change	ed		
PMZB290UN v.1	20120511	Product data sheet	-	-		

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#### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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